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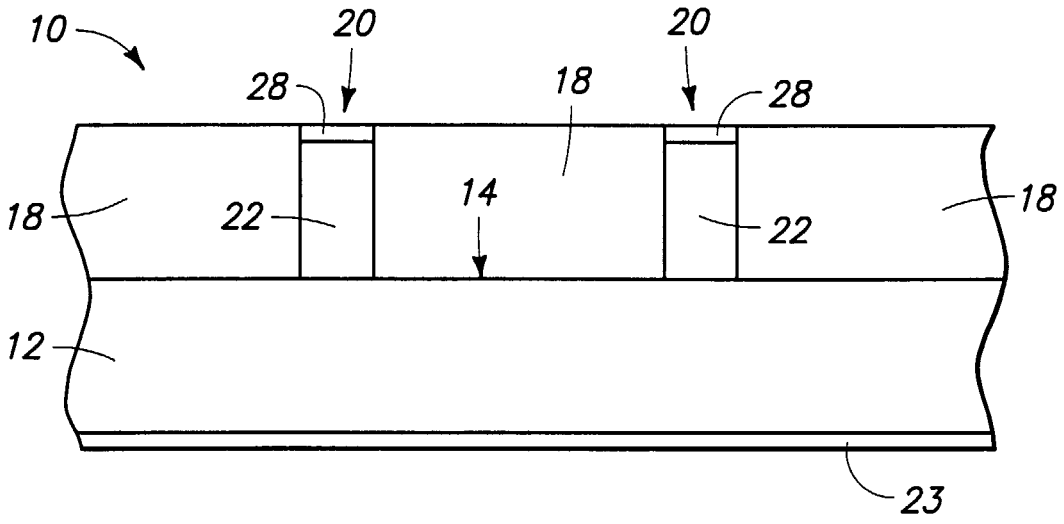
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(54) Title: RUTHENIUM SILICIDE PROCESSING METHODS



(57) Abstract: The invention includes methods of processing ruthenium silicide. In one implementation, a ruthenium silicide processing method sequentially includes forming ruthenium silicide (24, 26) over front and back sides of a semiconductor substrate. The backside ruthenium silicide is exposed to a chlorine and fluorine containing aqueous solution effective to remove at least some ruthenium silicide therefrom. Then, the substrate backside is exposed to an aqueous ruthenium oxide etchant solution. Then, the substrate backside is exposed to an aqueous hydrofluoric acid containing solution.

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